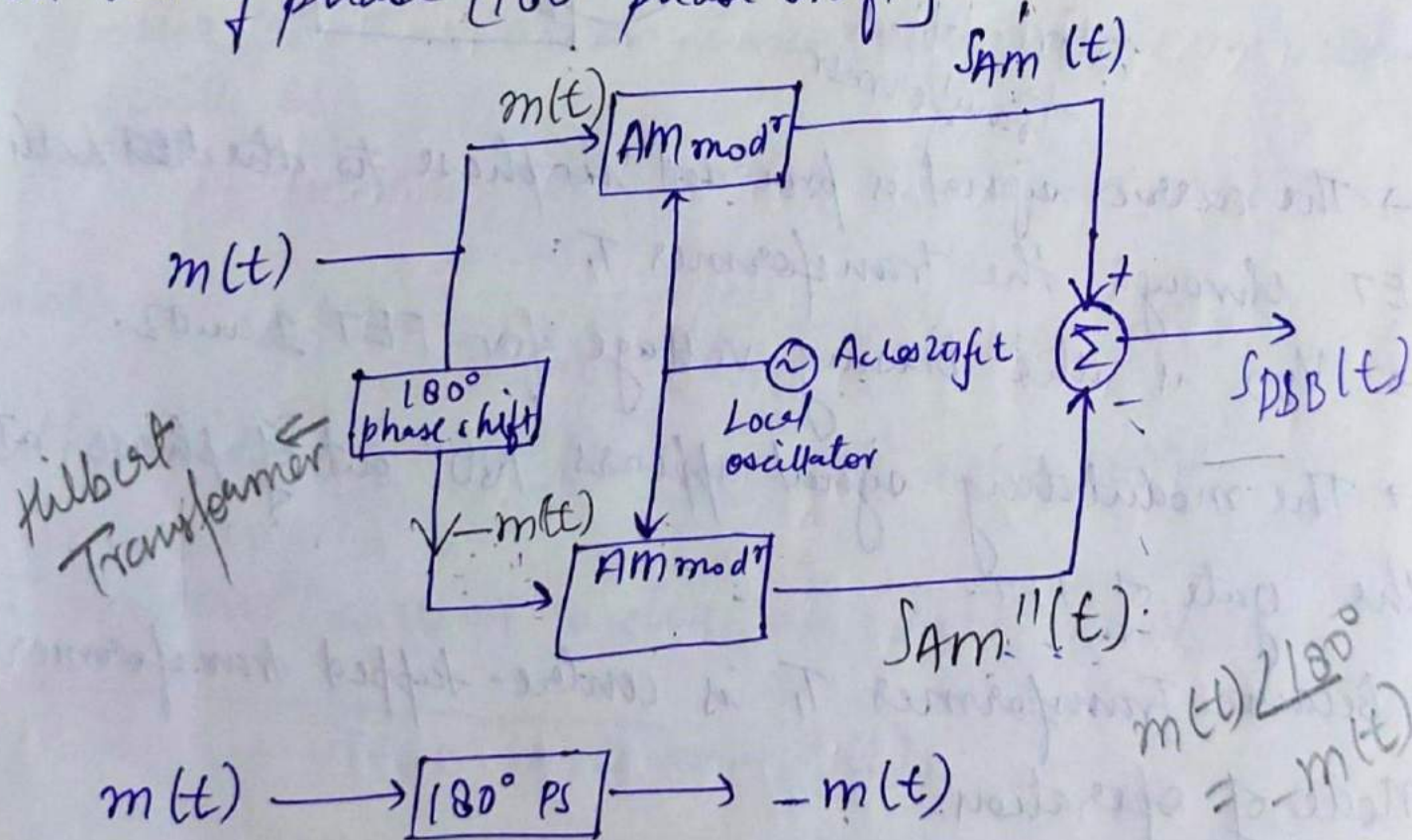


② Balanced Modulator →

→ In this two product modulators are used.

→ Modulating signals are provided to the PM in out of phase [180° phase shift]



Thus

$$S_{Am}'(t) = A_c [1 + k_a \cdot m(t)] \cos 2\pi f_c t$$

$$S_{Am}''(t) = A_c [1 - k_a \cdot m(t)] \cos 2\pi f_c t$$

$$S_{DSB}(t) = S_{Am}'(t) - S_{Am}''(t)$$

$$= A_c [1 + k_a \cdot m(t)] \cos 2\pi f_c t$$

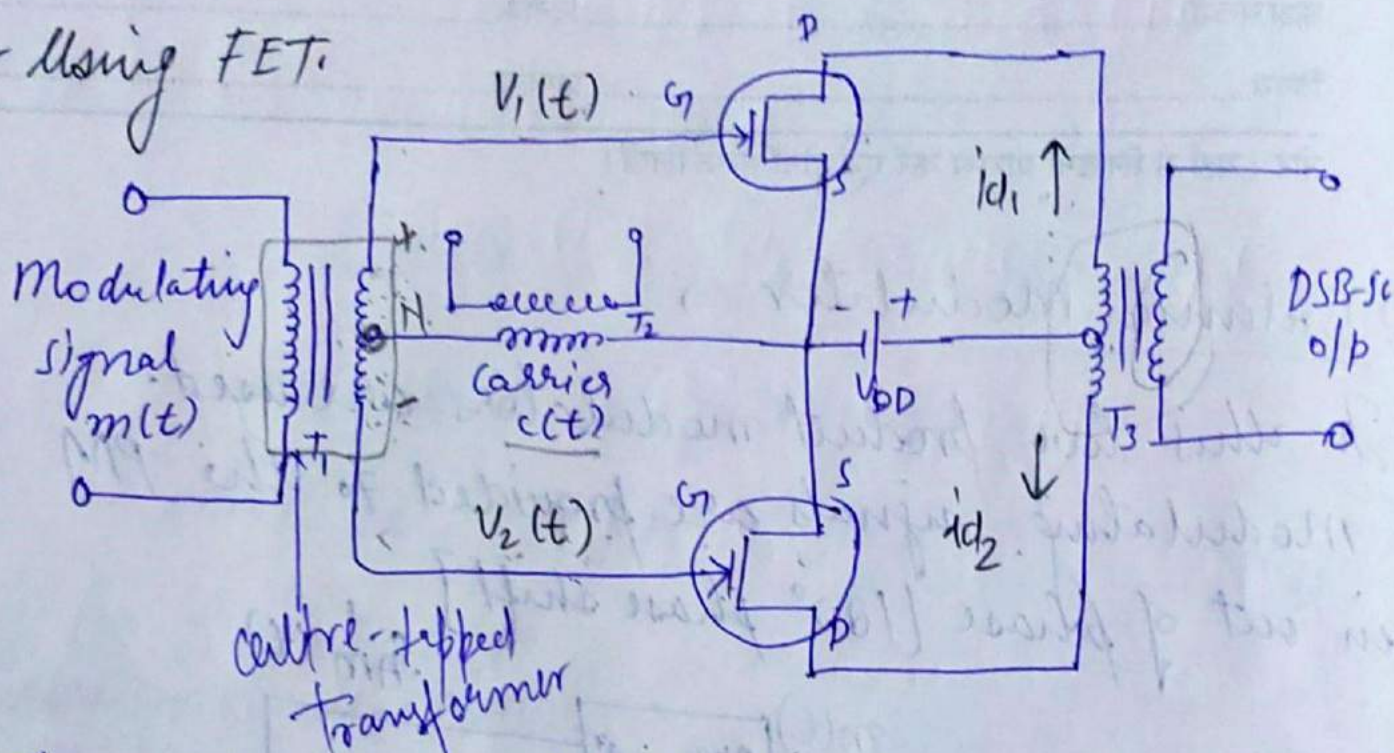
$$- A_c [1 - k_a \cdot m(t)] \cos 2\pi f_c t$$

$$S_{DSB}(t) = 2 \cdot A_c \cdot k_a \cdot m(t) \cdot \cos 2\pi f_c t$$

$$\Rightarrow S_{DSB}(t) = A_c' \cdot m(t) \cdot \cos 2\pi f_c t \quad \checkmark$$

where $A_c' = 2 A_c \cdot k_a$

i) - Using FET.



→ The carrier signal is provided in-phase to ~~the FET~~ both FET through the transformer T_2 .

→ V_{DD} is the biasing voltage for FET 1 and 2.

→ The modulating signal appears 180° out of phase at the gate of FET.

→ Because Transformer T_1 is centre-tapped transformer.
Mode of operation

(1) Absence of modulating signal.

Since $m(t) = 0$,

$$V_1(t) = V_2(t) = c(t)$$

→ $V_1(t)$ and $V_2(t)$ are in-phase.

→ So the drain current developed (i_{d1} and i_{d2}) will be equal and in-phase to each other.

- At transformer T_3 , the drains are in equal amplitude and phase, but are in opposite direction,
- So the net resultant voltage in the secondary winding of T_3 will be zero.
- And thus the carrier is suppressed.

② When modulating signal is present
since $m(t) \neq 0$,

$$V_1(t) = V_c(t) + m(t)$$

$$V_2(t) = c(t) - m(t)$$

Thus since FET is a non-linear device, the $V-i$ relation will be

$$i = a_1 V(t) + a_2 V(t)^2 + a_3 V(t)^3 + \dots$$

thus
$$i_{d1}(t) = a_1 V_1(t) + a_2 V_1(t)^2 + a_3 V_1(t)^3 + \dots$$

$$i_{d2}(t) = a_1 V_2(t) + a_2 V_2(t)^2 + a_3 V_2(t)^3 + \dots$$

Net resultant current due to $i_{d1}(t)$ and $i_{d2}(t)$ will be

$$i(t) = i_{d1}(t) - i_{d2}(t)$$

$$i(t) = a_1 (V_1(t) - V_2(t)) + a_2 (V_1(t)^2 - V_2(t)^2) + a_3 (V_1(t)^3 - V_2(t)^3) + \dots$$

$$= a_1 (2m(t)) + a_2 (c^2(t) + m^2(t)) + a_3 + \dots$$

$$= \underbrace{a_1 (2m(t))}_1 \underbrace{+ a_2 (4c(t) \cdot m(t))}_2 + \underbrace{a_3 + \dots}_3$$

1 f_m 2 $f_c \pm f_m$ 3

using a BPF of passband from $(f_c - f_m)$ to $(f_c + f_m)$ the higher frequency and the lower frequency terms are eliminated and finally only ②-term is through BPF and thus we have

$$S_{DSB}(t) = 4q_2 \cdot A_c \cdot m(t) \cos 2\pi f_c t$$

$$S_{DSB}(t) = A_c' m(t) \cos 2\pi f_c t$$

$$\text{where } A_c' = 4q_2 \cdot A_c$$

③ Collector Modulator

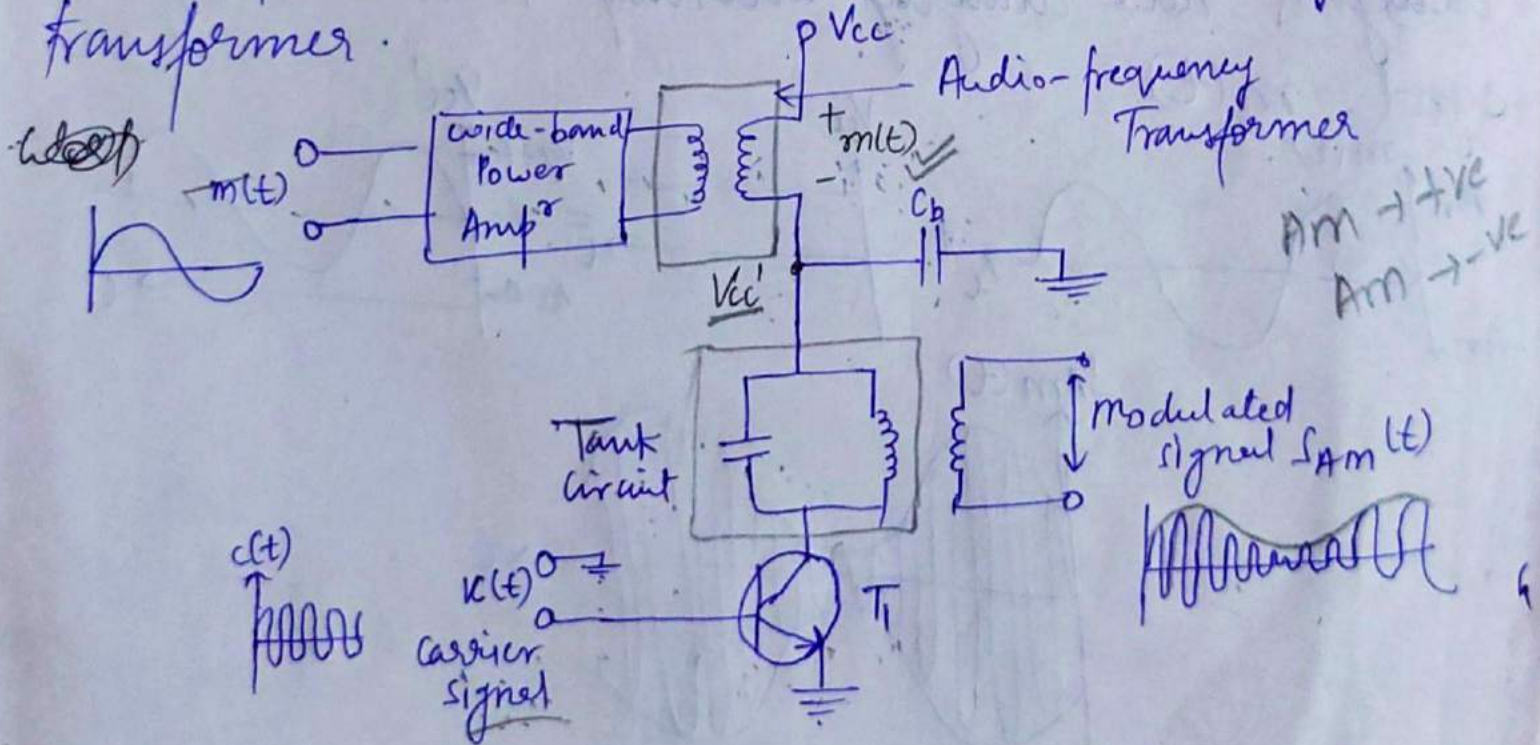
- High level AM modulation technique.
- Modulating signal and carrier signal are amplified before modulation.
- The output AM wave is obtained from the collector terminal of BJT, hence it is called collector modulator.
- Carrier signal is applied at the base-terminal of the transistor T_1 .
- Transistor T_1 acts as a RF class-C amplifier, to amplify the carrier signal.
- V_{cc} is ^{a DC} collector supply, used for biasing of T_1 .

→ Modulating signal is amplified using a wide-band power amplifier, and then it is applied at the primary winding (coil) of ~~the~~ a audio-frequency transformer (20 Hz - 20 kHz).

→ Tuned LC circuit is used to remove distortions from the class-C amplifier.

Working:

→ The bypass capacitor C_b prevents the high frequency carrier pulses to reach to the audio-frequency transformer.



Working.

- The amplified modulating signal $m(t)$ appears at the secondary winding of the AF-transformer.
- V_{cc} and $m(t)$ appear in series and so they get added or subtracted depending upon the amplitude. (added if A_m is +ve, subtracted if A_m is -ve).
- So the supply voltage to T_1 , V_{cc}' will now be equal to
$$V_{cc}' = V_{cc} + m(t)$$

and V_{cc}' will vary according to the $m(t)$.
- Now, due to the varying supplying voltage V_{cc}' , the amplitude of the current pulses will also vary according to V_{cc}' .
- As a result, the amplitude of the carrier sine wave ~~change~~ is now changing according to the message signal $m(t)$.

